

Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

Instead of http://www.nxp.com, http://www.nxp.com, http://www.nexperia.com/, http://www.nexperia.com/, use http://www.nexperia.com/

Instead of sales.addresses@www.nxp.com or sales.addresses@www.semiconductors.philips.com, use salesaddresses@nexperia.com (email)

Replace the copyright notice at the bottom of each page or elsewhere in the document, depending on the version, as shown below:

- © NXP N.V. (year). All rights reserved or © Koninklijke Philips Electronics N.V. (year). All rights reserved

Should be replaced with:

- © Nexperia B.V. (year). All rights reserved.

If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET

PDTA144W series PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

Product data sheet Supersedes data of 2004 Mar 23 2004 Aug 05



PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

PDTA144W series

FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- · Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V_{CEO}	collector-emitter voltage	_	-50	V
Io	output current (DC)	_	-100	mA
R1	bias resistor	47	_	kΩ
R2	bias resistor	22	_	kΩ

DESCRIPTION

PNP resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TVDE NUMBER	PAC	KAGE	MARKING CORE	NDN COMPLEMENT
TYPE NUMBER	PHILIPS EIAJ MARKING CO		MARKING CODE	NPN COMPLEMENT
PDTA144WE	SOT416	SC-75	5D	PDTC144WE
PDTA144WEF	SOT490	SC-89	2E	PDTC144WEF
PDTA144WK	SOT346	SC-59	46	PDTC144WK
PDTA144WM	SOT883	SC-101	F8	PDTC144WM
PDTA144WS	SOT54 (TO-92)	SC-43	TA144W	PDTC144WS
PDTA144WT	SOT23	_	*43 ⁽¹⁾	PDTC144WT
PDTA144WU	SOT323	SC-70	*28 ⁽¹⁾	PDTC144WU

Note

^{1. * =} p: Made in Hong Kong.

^{* =} t: Made in Malaysia.

^{* =} W: Made in China.

PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

PDTA144W series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TVDE NUMBER	CIMPLIFIED OUTLINE AND CYMPOL	PINNING		
TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION	
PDTA144WS	1 R1 R2 3 MAM338	1 2 3	base collector emitter	
PDTA144WE PDTA144WEF PDTA144WK PDTA144WT PDTA144WU	3 1 R1 1 R2 1 R2 Top view MDB271	1 2 3	base emitter collector	
PDTA144WM	2 R1 3 Bottom view ADB267	1 2 3	base emitter collector	

PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

PDTA144W series

ORDERING INFORMATION

TYPE NUMBER	PACKAGE						
ITPE NUMBER	NAME	NAME DESCRIPTION					
PDTA144WE	_	plastic surface mounted package; 3 leads	SOT416				
PDTA144WEF	_	plastic surface mounted package; 3 leads	SOT490				
PDTA144WK	_	plastic surface mounted package; 3 leads	SOT346				
PDTA144WM	_	leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm	SOT883				
PDTA144WS	_	plastic single-ended leaded (through hole) package; 3 leads	SOT54				
PDTA144WT	_	plastic surface mounted package; 3 leads	SOT23				
PDTA144WU	_	plastic surface mounted package; 3 leads	SOT323				

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-50	V
V _{CEO}	collector-emitter voltage	open base	_	-50	V
V _{EBO}	emitter-base voltage	open collector	_	-10	V
VI	input voltage				
	positive		_	+10	V
	negative		_	-40	V
Io	output current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C;$			
	SOT54	note 1	_	500	mW
	SOT23	note 1	_	250	mW
	SOT346	note 1	_	250	mW
	SOT323	note 1	_	200	mW
	SOT416	note 1	_	150	mW
	SOT490	notes 1 and 2	_	250	mW
	SOT883	notes 2 and 3	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

PDTA144W series

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	830	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

Note

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions.; FR4 with 60 μm copper strip line.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	_	_	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}; T_{j} = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}$	_	_	-110	μΑ
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	60	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-150	mV
$V_{i(off)}$	input-off voltage	$I_C = -100 \mu A; V_{CE} = -5 V$	_	-1.7	-1.2	V
$V_{i(on)}$	input-on voltage	$I_C = -2 \text{ mA}; V_{CE} = -0.3 \text{ V}$	-4	-2.7	_	V
R1	input resistor		33	47	61	kΩ
R2 R1	resistor ratio		0.37	0.47	0.57	
C _c	collector capacitance	$I_E = I_e = 0 \text{ A}; V_{CB} = -10 \text{ V};$ f = 1 MHz	_	_	3	pF

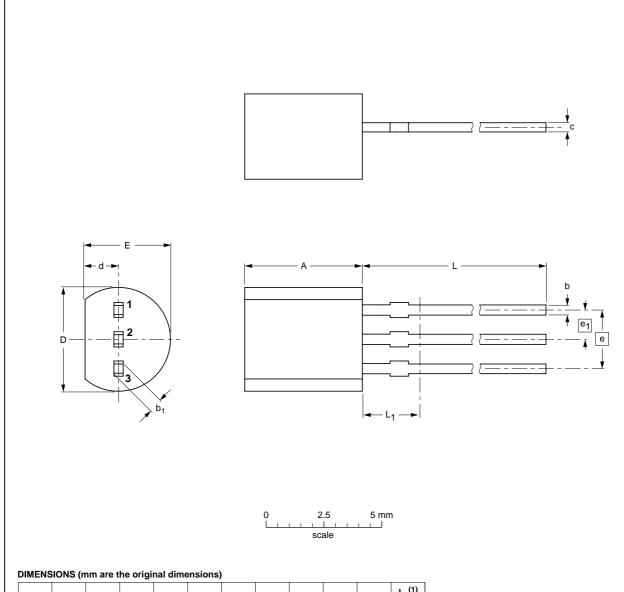
PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

PDTA144W series

PACKAGE OUTLINES

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

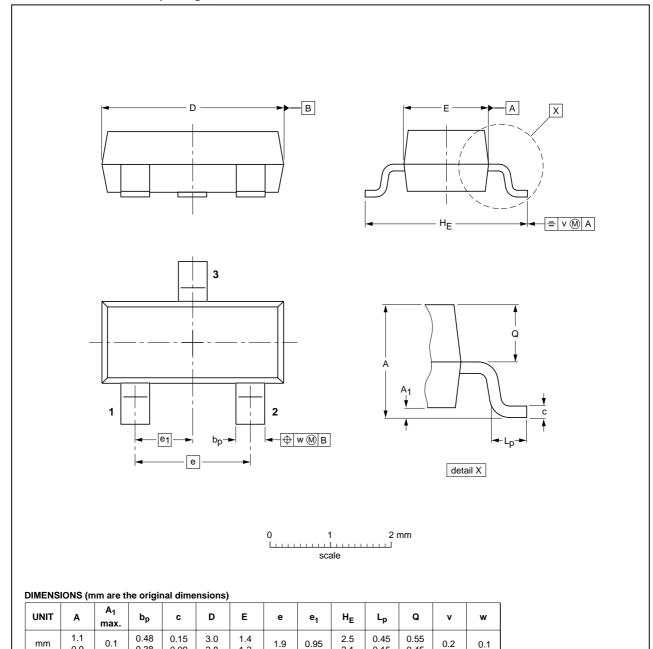
OUTLINE		REFER	ENCES	EUROPEAN ISSUE DATE				
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE			
SOT54		TO-92	SC-43A		-04-06-28- 04-11-16			

PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

PDTA144W series

Plastic surface-mounted package; 3 leads

SOT23



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT23		TO-236AB			-04-11-04- 06-03-16	

2004 Aug 05 7

0.38

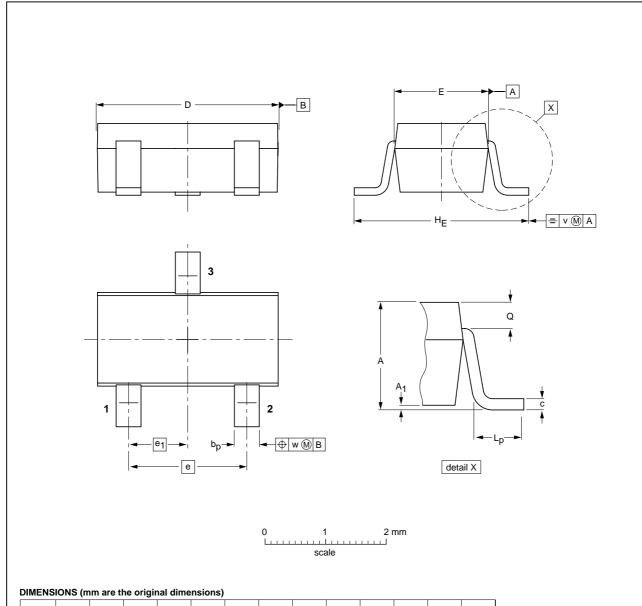
0.9

PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

PDTA144W series

Plastic surface-mounted package; 3 leads

SOT346



UNIT	Α	A ₁	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
mm	1.3 1.0	0.1 0.013	0.50 0.35	0.26 0.10	3.1 2.7	1.7 1.3	1.9	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2

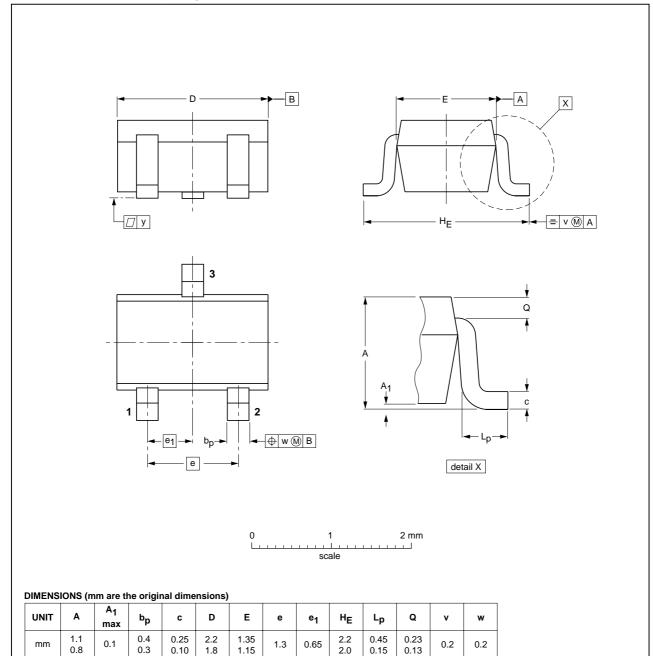
OUTLINE		REFER	ENCES	EUROPEAN	ICCUIT DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT346		TO-236	SC-59A		-04-11-11 06-03-16	

PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

PDTA144W series

Plastic surface-mounted package; 3 leads

SOT323



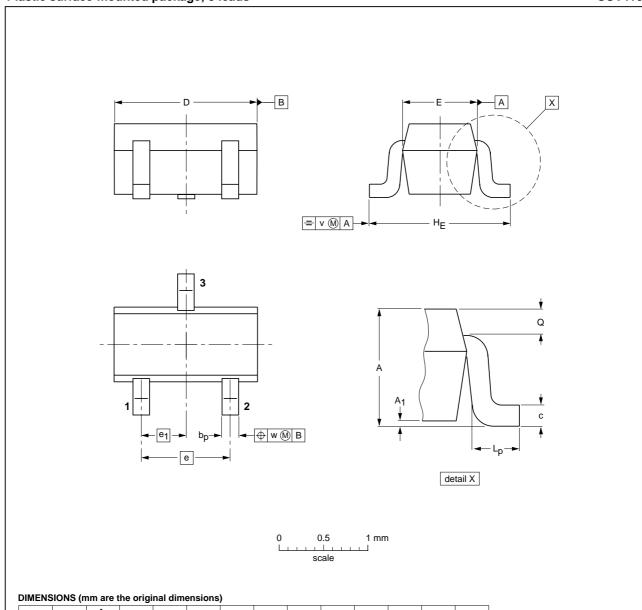
OUTLINE		EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT323			SC-70			04-11-04 06-03-16

PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

PDTA144W series

Plastic surface-mounted package; 3 leads

SOT416



UNIT	Α	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	ø	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

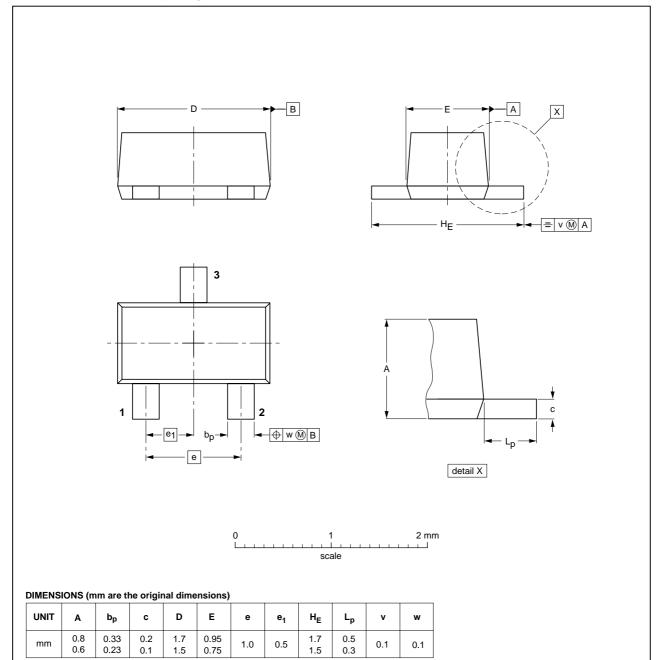
OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT416			SC-75			04-11-04 06-03-16	

PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

PDTA144W series

Plastic surface-mounted package; 3 leads

SOT490



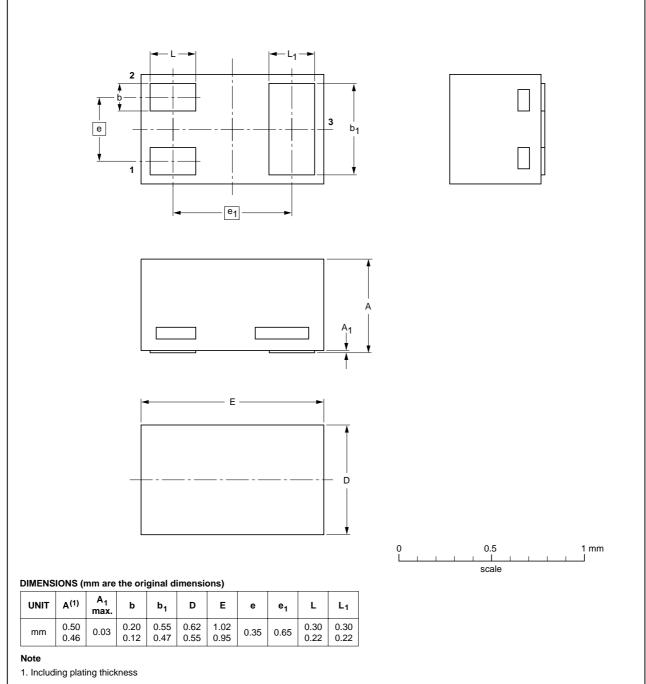
	REFER	EUROPEAN	ISSUE DATE		
IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
		SC-89			05-07-28 06-03-16
	IEC			IEC JEDEC JEITA	IEC JEDEC JEITA PROJECTION

PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

PDTA144W series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION		
SOT883			SC-101		03-02-05 03-04-03	

PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

PDTA144W series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

DISCLAIMERS

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions

above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
For sales offices addresses send e-mail to: salesaddresses@nxp.com

© NXP B.V. 2009

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

 Printed in The Netherlands
 R75/07/pp14
 Date of release: 2004 Aug 05
 Document order number: 9397 750 13662

